

Reg.No. \_\_\_\_\_



# Karunya UNIVERSITY

(Karunya Institute of Technology & Sciences)  
(Declared as Deemed-to-be University under Sec.3 of the UGC Act, 1956)

## End Semester Examination – Nov/Dec – 2016

Code : **14EE3001**  
Sub. Name : **POWER SEMICONDUCTOR DEVICES**

Semester : **2016-17 ODD**  
Duration : **3hrs**  
Max. marks : **100**

### ANSWER ALL QUESTIONS (5 x 20 = 100 Marks)

Q. No.	Sub Div.	Questions	Course Outcome	Marks
1.	a.	Compare and Contrast ideal and practical characteristics of switch	CO1	10
	b.	List the different types of power diodes and explain.	CO1	10
(OR)				
2.	a.	Discuss the series and parallel operation of diodes	CO1	10
	b.	Briefly explain the control characteristics of power devices.	CO1	10
3.	a.	Illustrate the switching performance of BJT in detail..	CO1	10
	b.	Compare and Contrast PMOSFET with BJT.	CO1	10
(OR)				
4.	a.	A bipolar transistor has current gain $\beta=40$ . The load resistance $R_C=10\ \Omega$ , dc supply voltage $V_{CC}=130\text{ V}$ and input voltage to base circuit, $V_B=10\text{ V}$ . For $V_{CES}=1.0\text{ V}$ and $V_{BES}=1.5\text{ V}$ , calculate: (i) the value of $R_B$ for operation in the saturated state (ii) the value of $R_B$ for an overdrive factor 5 (iii) forced-current gain and (iv) power loss in the transistor for both parts (i) and (ii)	CO2	20
5.	a.	In detail, explain the constructional details of PMOSFET.	CO2	15
	b.	Compare and Contrast IGBT with PMOSFET.	CO2	5
(OR)				
6.	a.	In detail, explain the constructional details of IGBT.	CO3	15
	b.	Compare and Contrast IGBT with BJT.	CO3	5
7.	a.	Explain the construction and characteristics of SIT.	CO3	10
	b.	Illustrate the series and parallel operation of thyristor	CO3	10
(OR)				
8.	a.	Illustrate the switching characteristics of thyristor	CO3	10
	b.	Briefly, explain the turn on methods of thyristor.	CO3	10
<b><u>Compulsory:</u></b>				
9.	a.	Explain the switching characteristics of GTO	CO3	10
	b.	Briefly explain the features of TRIAC.	CO3	10

ALL THE BEST